

# CMS16N06D-HF

**N-Channel**  
**RoHS Device**  
**Halogen Free**



## Features

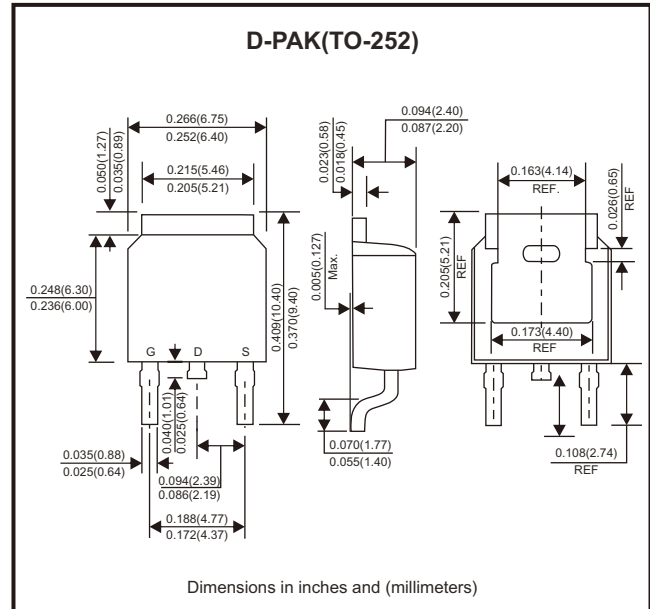
- Low reverse transfer capacitance.
- High switching speed.
- Improved dv/dt capability.
- 100% EAS guaranteed.
- Green device available.

## Mechanical data

- Case: D-PAK/TO-252 standard package, molded plastic.

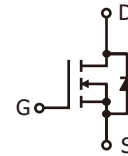
## Description

The CMS16N06D is the highest performance N-ch MOSFETs with super high dense cell density for extremely low RDS(ON) and gate charge for most of the synchronous buck converter applications. The CMS16N06D meet the ROHS and Green Product require ment, 100% EAS guaranteed with full function reliability approved.



## Circuit Diagram

- G : Gate
- D : Drain
- S : Source



## Maximum Ratings (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Value	Unit
Drain-source voltage		V <sub>DS</sub>	60	V
Gate-source voltage		V <sub>GS</sub>	±20	V
Continuous drain current (Note 1)	T <sub>C</sub> = 25°C	I <sub>D</sub>	16	A
	T <sub>C</sub> = 100°C	I <sub>D</sub>	10	
Pulsed drain current (Note 1, 2)	T <sub>C</sub> = 25°C	I <sub>DM</sub>	64	A
Continuous drain current	T <sub>A</sub> = 25°C	I <sub>D</sub>	4.4	A
	T <sub>A</sub> = 70°C	I <sub>D</sub>	3.5	
Total power dissipation (Note 4)	T <sub>C</sub> = 25°C	P <sub>D</sub>	27	W
	T <sub>A</sub> = 25°C	P <sub>D</sub>	2	
Single pulse avalanche energy, L=0.1mH (Note 3)		E <sub>AS</sub>	11	mJ
Single pulse avalanche current, L=0.1mH (Note 3)		I <sub>AS</sub>	15	A
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Thermal Data

Parameter	Conditions	Symbol	Max. Value	Unit
Thermal resistance junction-ambient (Note 1)	Steady state	R <sub>θJA</sub>	62.5	°C/W
Thermal resistance junction-case (Note 1)	Steady state	R <sub>θJC</sub>	4.6	°C/W

## Electrical Characteristics (at T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Drain-source breakdown voltage	BV <sub>DSS</sub>	60			V	V <sub>GS</sub> = 0, I <sub>D</sub> = 250μA
Gate threshold voltage	V <sub>GS(th)</sub>	1.0	1.8	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Gate-source leakage current	I <sub>GSS</sub>			±100	nA	V <sub>GS</sub> = ±20V
Drain-source leakage current	I <sub>DSS</sub>			1	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0
Static drain-source on-resistance (Note 2)	R <sub>DS(on)</sub>		37	50	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 8A
			42	60		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4A
Total gate charge (Note 2)	Q <sub>g</sub>		14		nC	I <sub>D</sub> = 4A, V <sub>DS</sub> = 30V, V <sub>GS</sub> = 10V
Gate-source charge	Q <sub>gs</sub>		2.9			
Gate-drain ("Miller") charge	Q <sub>gd</sub>		2.3			
Turn-on delay time (Note 2)	t <sub>d(on)</sub>		3.9		ns	V <sub>DS</sub> = 30V, I <sub>D</sub> = 1A, V <sub>GS</sub> = 10V, R <sub>G</sub> = 3.3Ω
Rise time	t <sub>r</sub>		13			
Turn-off delay time	t <sub>d(off)</sub>		23			
Fall time	t <sub>f</sub>		6.7			
Input capacitance	C <sub>iss</sub>		815		pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V, f = 1MHz
Output capacitance	C <sub>oss</sub>		379			
Reverse transfer capacitance	C <sub>rss</sub>		110			
<b>Guaranteed avalanche characteristics</b>						
Single pulse avalanche energy (Note 5)	EAS	3.2			mJ	V <sub>DD</sub> = 25V, L = 0.1mH, I <sub>AS</sub> = 8A
<b>Source-drain diode</b>						
Diode forward voltage (Note 2)	V <sub>SD</sub>		0.73	1.0	V	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25°C
Continuous source current (Note 1, 6)	I <sub>S</sub>			16	A	

- Notes: 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.  
 2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%.  
 3. The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=15A.  
 4. The power dissipation is limited by 150°C junction temperature.  
 5. The min. value is 100% EAS tested guarantee.  
 6. The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

## Rating and Characteristic Curves (CMS16N06D-HF)

### Typical Characteristics

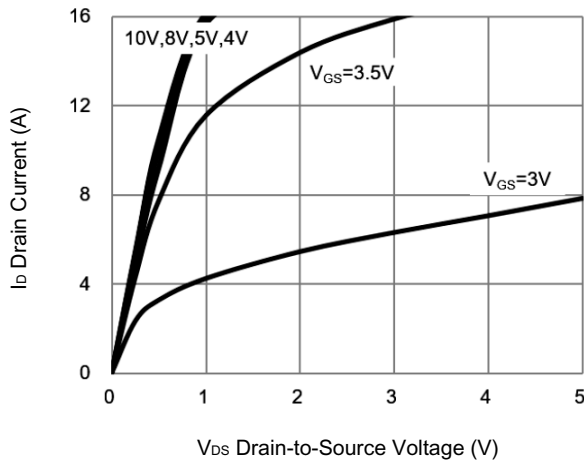


Fig.1 Typical Output Characteristics

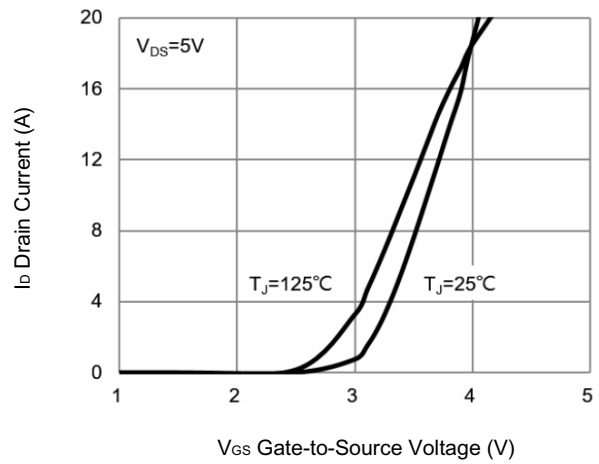


Fig.2 Transfer Characteristics

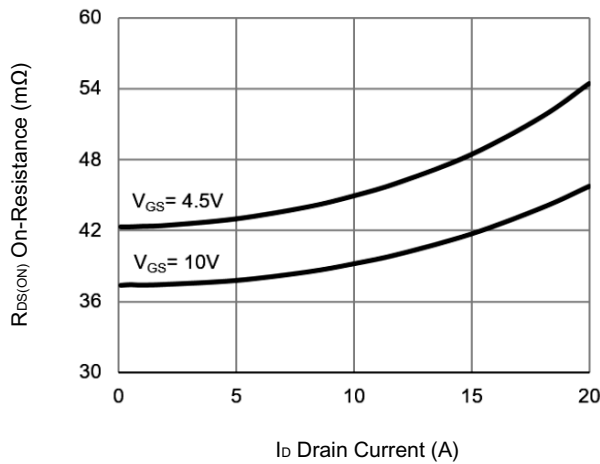


Fig.3 On-Resistance vs. Drain Current

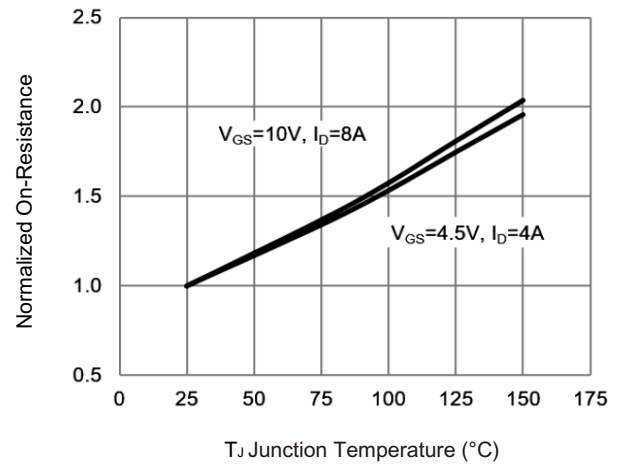


Fig.4 Normalized  $R_{DS(on)}$  vs.  $T_J$

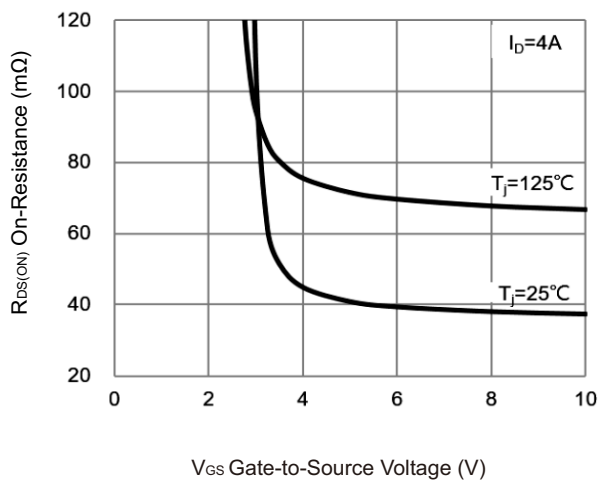


Fig.5 On-Resistance vs. G-S Voltage

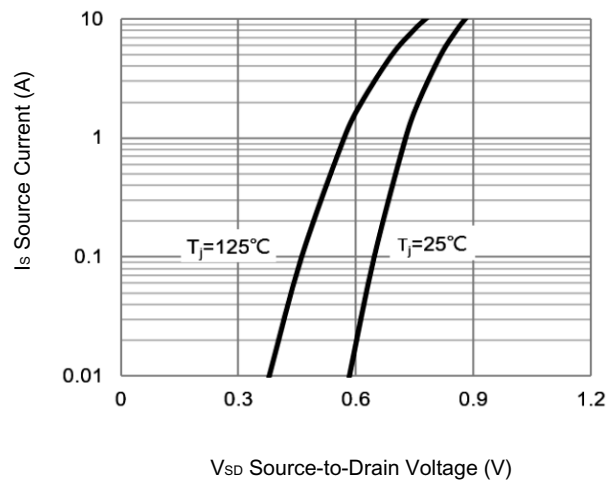


Fig.6 Forward Characteristics of Reverse

Company reserves the right to improve product design, functions and reliability without notice.

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## Rating and Characteristic Curves (CMS16N06D-HF)

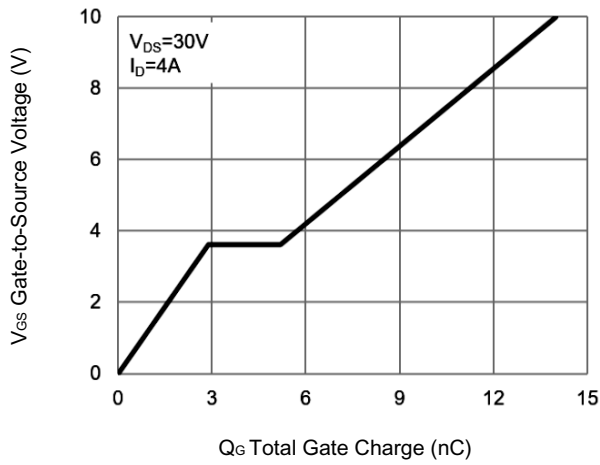


Fig.7 Gate Charge Characteristics

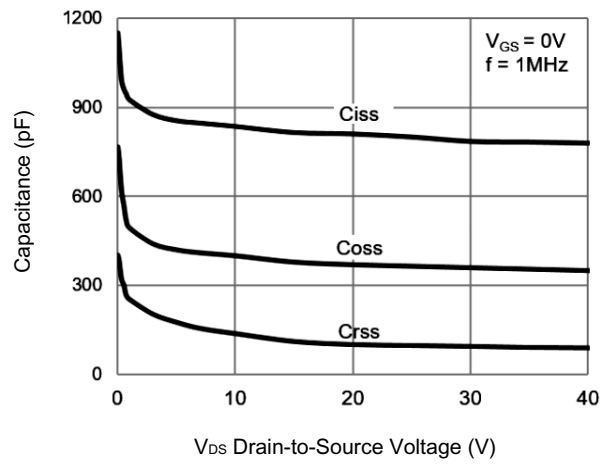


Fig.8 Capacitance Characteristics

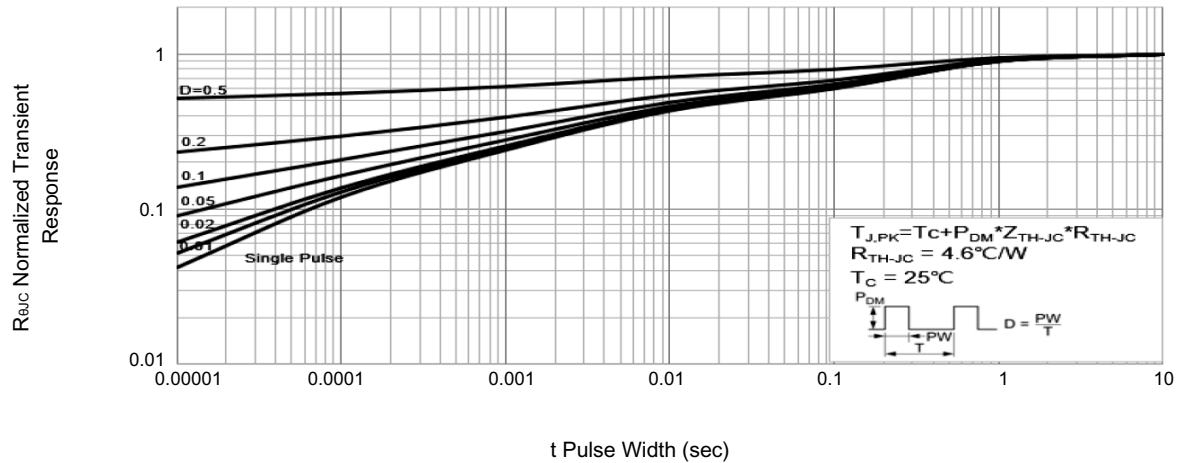


Fig.9 Normalized Maximum Transient Thermal Impedance

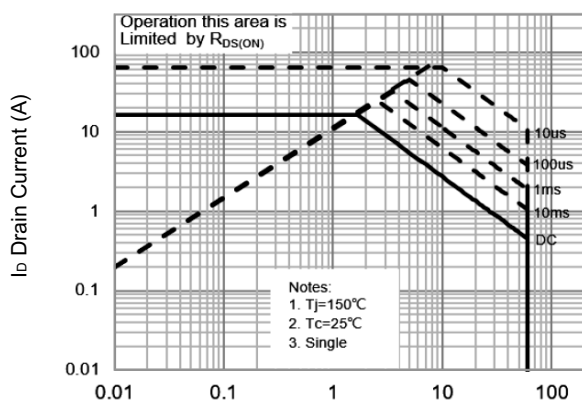


Fig.10 Safe Operating Area

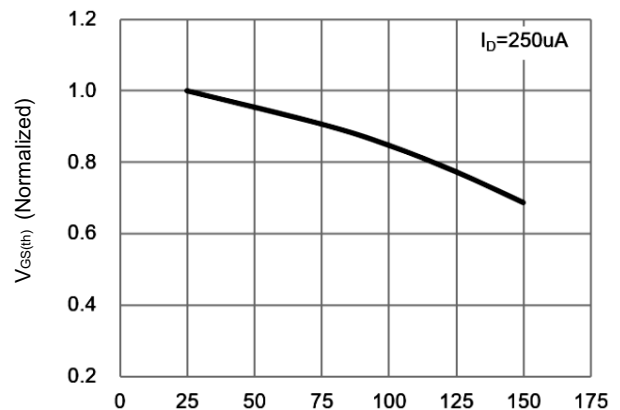
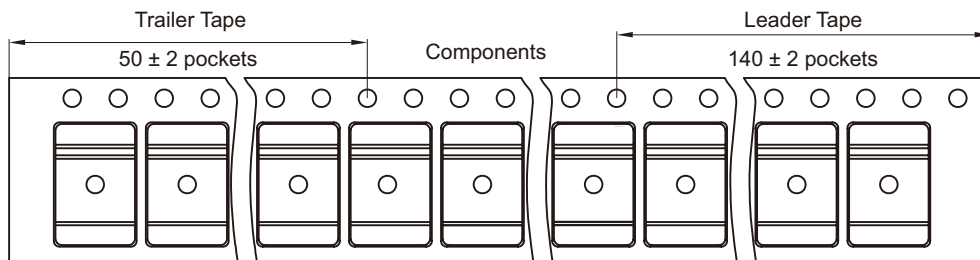
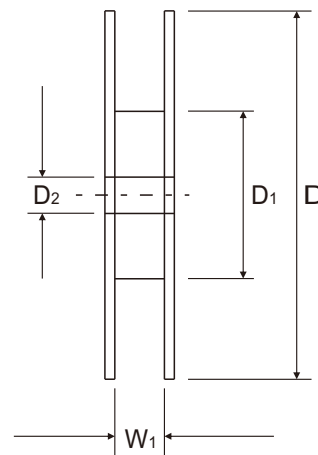
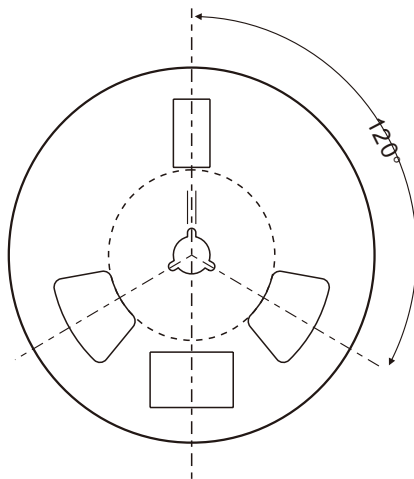
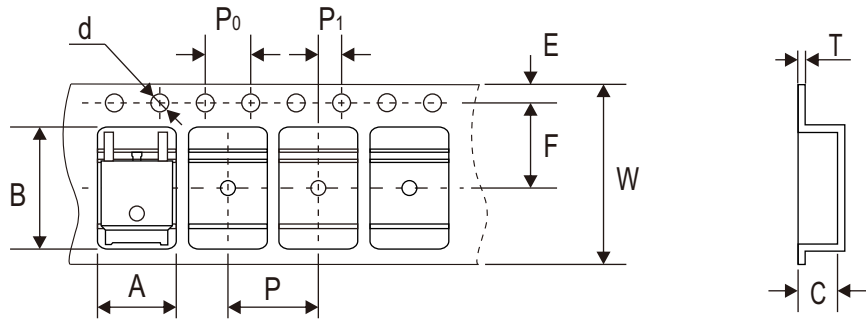


Fig.11 Normalized  $V_{GS(th)}$  vs. Temperature

Reel Taping Specification



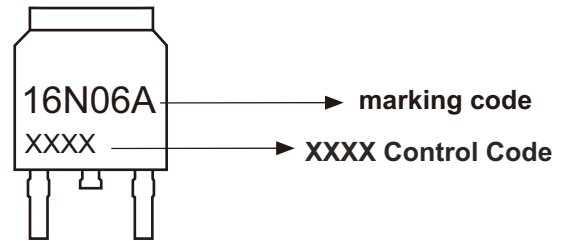
TO-252 (D-PAK)	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	6.90 ± 0.10	10.50 ± 0.10	2.78 ± 0.10	1.50 ± 0.10	330 ± 1.00	100.00 ± 0.50	13.20 ± 0.20
	(inch)	0.272 ± 0.004	0.413 ± 0.004	0.109 ± 0.004	0.059 ± 0.004	12.992 ± 0.039	3.937 ± 0.020	0.520 ± 0.008

TO-252 (D-PAK)	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	7.50 ± 0.10	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.25 ± 0.02	16.00 ± 0.10	16.40 ± 0.02
	(inch)	0.069 ± 0.004	0.295 ± 0.004	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.010 ± 0.001	0.630 ± 0.004	0.646 ± 0.01

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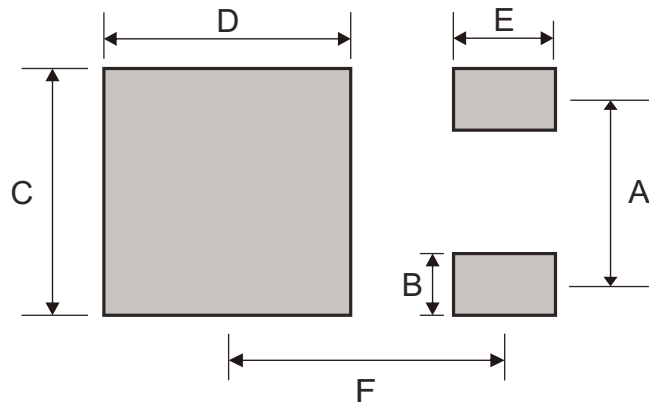
## Marking Code

Part Number	Marking Code
CMS16N06D-HF	16N06A



## Suggested P.C.B. PAD Layout

SIZE	TO-252 / DPAK	
	(mm)	(inch)
A	4.60	0.181
B	1.40	0.055
C	6.00	0.236
D	6.50	0.256
E	3.00	0.118
F	6.25	0.246



Note: 1. The pad layout is for reference purposes only.

## Standard Packaging

Case Type	REEL PACK	
	REEL ( pcs )	REEL SIZE (inch)
TO-252/D-PAK	2,500	13